

**TOSHIBA****1SS315**

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

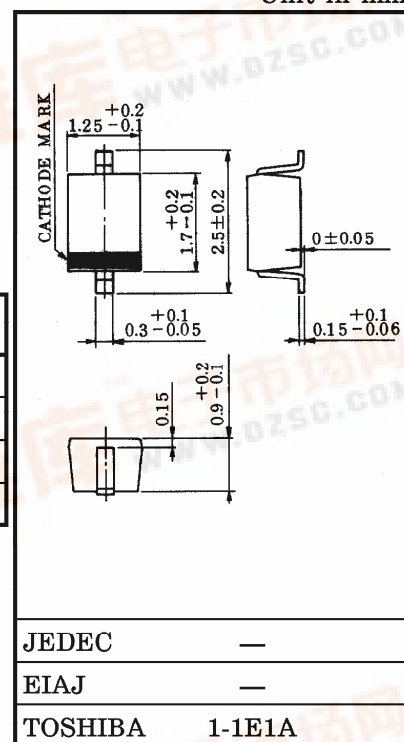
**1SS315**

UHF BAND MIXER APPLICATIONS.

Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	$V_{RM}$	5	V
Forward Current	$I_F$	30	mA
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_{stg}$	-55~125	°C



Weight : 0.004g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F$	$I_F = 2\text{mA}$	—	0.25	—	V
Forward Current	$I_F$	$V_F = 0.5\text{V}$	30	—	—	mA
Reverse Current	$I_R$	$V_R = 0.5\text{V}$	—	—	25	$\mu\text{A}$
Total Capacitance	$C_T$	$V_R = 0.2\text{V}$ , $f = 1\text{MHz}$	—	0.6	—	pF

Marking



961001FAA2

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